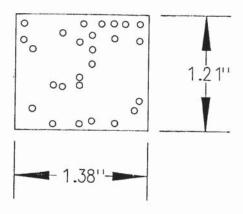
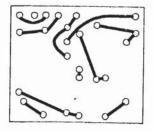
TOP VIEW

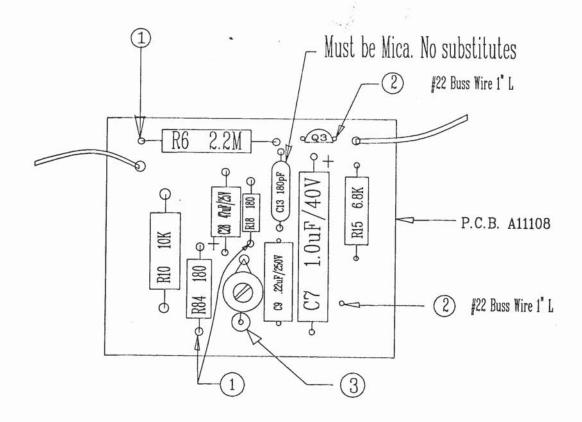


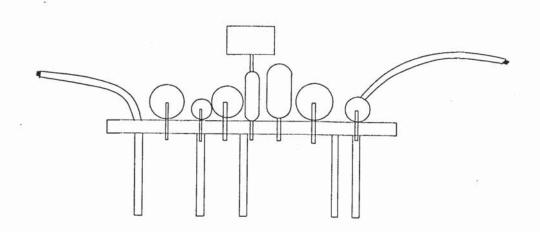
Component Side

BACK VIEW



Solder Side





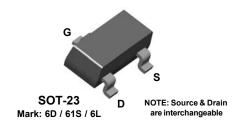
- 1 Indicates Leads Shall Not Be Cut Off At Board
- 2 Adding #22 Gauge Buss Wire With 1" Long
- 3 150 Ohms Resistor, R85A



2N5457 2N5458 2N5459

MMBF5457 MMBF5458 MMBF5459





N-Channel General Purpose Amplifier

This device is a low level audio amplifier and switching transistors, and can be used for analog switching applications. Sourced from Process 55.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{DG}	Drain-Gate Voltage	25	V
V _{GS}	Gate-Source Voltage	- 25	V
I _{GF}	Forward Gate Current	10	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

Thermal Characteristics TA = 25°C unless otherwise noted

Symbol	Characteristic	Max		Units
		2N5457-5459	*MMBF5457-5459	
P_D	Total Device Dissipation	625	350	mW
	Derate above 25°C	5.0	2.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

^{*}Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

¹⁾ These ratings are based on a maximum junction temperature of 150 degrees C.

2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

N-Channel General Purpose Amplifier

(continued)

Electrical	Characteristic);
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TA = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
					•	

OFF CHARACTERISTICS

$V_{(BR)GSS}$	Gate-Source Breakdown Voltage	$I_G = 10 \mu A, V_{DS} = 0$	- 25			V
I _{GSS}	Gate Reverse Current	V _{GS} = -15 V, V _{DS} = 0 V _{GS} = -15 V, V _{DS} = 0, T _A = 100°C	:		- 1.0 - 200	nA nA
V _{GS(off)}	Gate-Source Cutoff Voltage	V _{DS} = 15 V, I _D = 10 nA 5457 5458 5459	- 0.5 - 1.0 - 2.0		- 6.0 - 7.0 - 8.0	V V V
V _{GS}	Gate-Source Voltage	$\begin{array}{c} V_{DS} = 15 \text{ V}, \ I_D = 100 \ \mu\text{A} & \textbf{5457} \\ V_{DS} = 15 \text{ V}, \ I_D = 200 \ \mu\text{A} & \textbf{5458} \\ V_{DS} = 15 \text{ V}, \ I_D = 400 \ \mu\text{A} & \textbf{5459} \end{array}$		- 2.5 - 3.5 - 4.5		V V V

ON CHARACTERISTICS

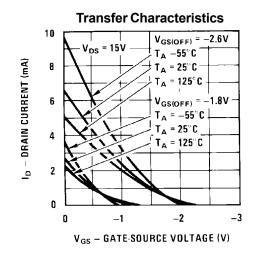
I _{DSS}	Zero-Gate Voltage Drain Current*	$V_{DS} = 15 \text{ V}, V_{GS} = 0$	5457	1.0	3.0	5.0	mA
	_		5458	2.0	6.0	9.0	mΑ
			5459	4.0	9.0	16	mA

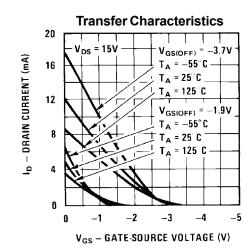
SMALL SIGNAL CHARACTERISTICS

9 _{fs}	Forward Transfer Conductance*	$V_{DS} = 15 \text{ V}, V_{GS} = 0, f = 1.0 \text{ kHz}$				
		5457 5458 5459	1000 1500 2000		5000 5500 6000	μmhos μmhos μmhos
gos	Output Conductance*	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 kHz		10	50	μmhos
Ciss	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz		4.5	7.0	pF
Crss	Reverse Transfer Capacitance	V _{DS} = 15 V, V _{GS} = 0, f = 1.0 MHz		1.5	3.0	pF
NF	Noise Figure	V_{DS} = 15 V, V_{GS} = 0, f = 1.0 kHz, R _G = 1.0 megohm, BW = 1.0 Hz			3.0	dB

^{*}Pulse Test: Pulse Width ≤ 300 ms, Duty Cycle ≤ 2%

Typical Characteristics

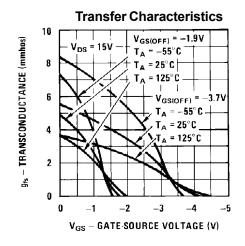


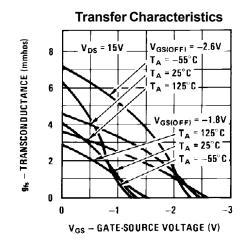


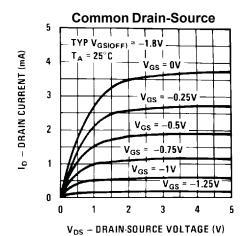
N-Channel General Purpose Amplifier

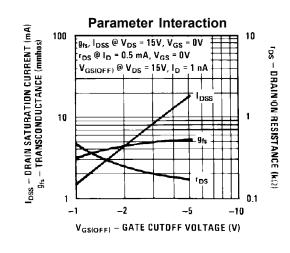
(continued)

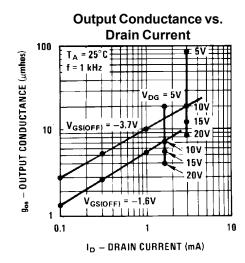
Typical Characteristics (continued)

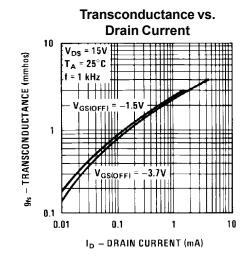








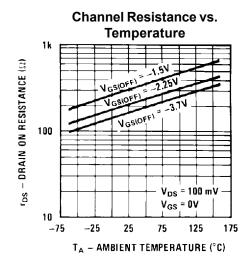


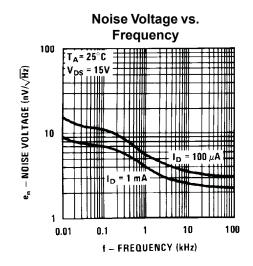


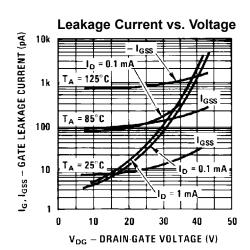
N-Channel General Purpose Amplifier

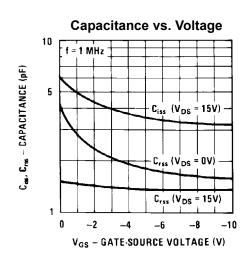
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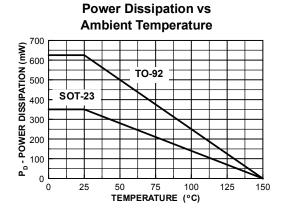
Typical Characteristics (continued)











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